

# MOSFET - SiC Power, Single N-Channel

## 1200 V, 160 mΩ, 17 A

### NTHL160N120SC1

#### Features

- Typ.  $R_{DS(on)} = 160 \text{ m}\Omega$
- Ultra Low Gate Charge ( $Q_{G(\text{tot})} = 34 \text{ nC}$ )
- Low Effective Output Capacitance ( $C_{oss} = 50 \text{ pF}$ )
- 100% UIL Tested
- These Devices are RoHS Compliant

#### Typical Applications

- UPS
- DC/DC Converter
- Boost Inverter

**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	1200	V
Gate-to-Source Voltage	$V_{GS}$	-15/+25	V
Recommended Operation Values of Gate-to-Source Voltage	$V_{GSop}$	-5/+20	V
Continuous Drain Current	Steady State	$I_D$	A
	$T_C = 25^\circ\text{C}$	17	A
Power Dissipation		$P_D$	W
Continuous Drain Current	Steady State	$I_D$	A
	$T_C = 100^\circ\text{C}$	12	A
Power Dissipation		$P_D$	W
Pulsed Drain Current (Note 2)	$T_A = 25^\circ\text{C}$	$I_{DM}$	A
Single Pulse Surge Drain Current Capability	$T_A = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$ , $R_G = 4.7 \Omega$	$I_{DSC}$	A
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	°C
Source Current (Body Diode)	$I_S$	11	A
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 23 \text{ A}$ , $L = 1 \text{ mH}$ ) (Note 3)	$E_{AS}$	128	mJ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Junction-to-Case (Note 1)	$R_{\theta JC}$	1.3	°C/W
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	°C/W

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3.  $E_{AS}$  of 128 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1 \text{ mH}$ ,  $I_{AS} = 16 \text{ A}$ ,  $V_{DD} = 120 \text{ V}$ ,  $V_{GS} = 18 \text{ V}$ .

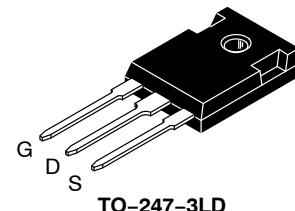
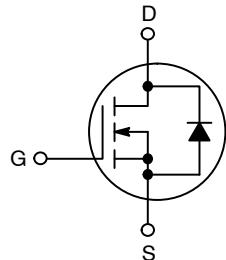


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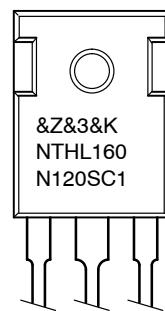
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
1200 V	160 mΩ @ 20 V	17 A

#### N-CHANNEL MOSFET



TO-247-3LD  
CASE 340CX

#### MARKING DIAGRAM



**&Z** = Assembly Plant Code  
**&3** = Date Code (Year & Week)  
**&K** = Lot  
**NTHL160N120SC1** = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NTHL160N120SC1

**ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 1 \text{ mA}$	1200	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}/T_J}$	$I_D = 1 \text{ mA}$ , referenced to $25^\circ\text{C}$	–	600	–	$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 1200 \text{ V}, T_J = 25^\circ\text{C}$	–	–	100	$\mu\text{A}$
		$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 1200 \text{ V}, T_J = 175^\circ\text{C}$	–	–	250	
Gate-to-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}} = +25/-15 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	–	–	$\pm 1$	$\mu\text{A}$

## ON CHARACTERISTICS

Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 2.5 \text{ mA}$	1.8	3.1	4.3	V
Recommended Gate Voltage	$V_{\text{GOP}}$		–5	–	+20	V
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 20 \text{ V}, I_D = 12 \text{ A}, T_J = 25^\circ\text{C}$	–	162	224	$\text{m}\Omega$
		$V_{\text{GS}} = 20 \text{ V}, I_D = 12 \text{ A}, T_J = 175^\circ\text{C}$	–	271	377	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}} = 10 \text{ V}, I_D = 12 \text{ A}$	–	3	–	S

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{\text{ISS}}$	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, V_{\text{DS}} = 800 \text{ V}$	–	665	–	pF
Output Capacitance	$C_{\text{OSS}}$		–	50	–	
Reverse Transfer Capacitance	$C_{\text{RSS}}$		–	5	–	
Total Gate Charge	$Q_{\text{G}(\text{tot})}$	$V_{\text{GS}} = -5/20 \text{ V}, V_{\text{DS}} = 600 \text{ V}, I_D = 16 \text{ A}$	–	34	–	nC
Threshold Gate Charge	$Q_{\text{G}(\text{th})}$		–	6	–	
Gate-to-Source Charge	$Q_{\text{GS}}$		–	12.5	–	
Gate-to-Drain Charge	$Q_{\text{GD}}$		–	9.6	–	
Gate Resistance	$R_G$		$f = 1 \text{ MHz}$	–	1.4	–

## SWITCHING CHARACTERISTICS

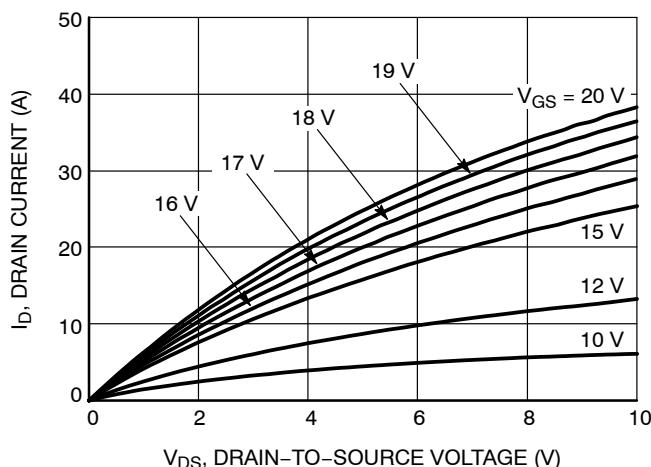
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = -5/20 \text{ V}, V_{\text{DS}} = 800 \text{ V}, I_D = 16 \text{ A}, R_G = 6 \Omega, \text{Inductive Load}$	–	11	–	ns
Rise Time	$t_r$		–	19	–	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		–	15	–	
Fall Time	$t_f$		–	8	–	
Turn-On Switching Loss	$E_{\text{ON}}$		–	200	–	$\mu\text{J}$
Turn-Off Switching Loss	$E_{\text{OFF}}$		–	–	34	
Total Switching Loss	$E_{\text{TOT}}$		–	234	–	

## DRAIN-SOURCE DIODE CHARACTERISTICS

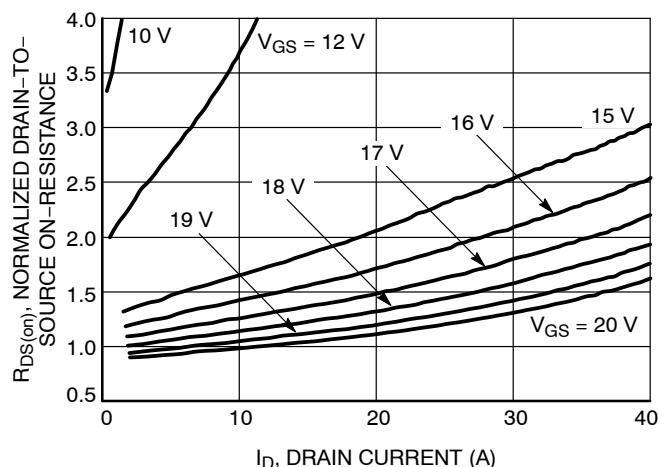
Continuous Drain-to-Source Diode Forward Current	$I_{\text{SD}}$	$V_{\text{GS}} = -5 \text{ V}, T_J = 25^\circ\text{C}$	–	–	11	A
Pulsed Drain-to-Source Diode Forward Current (Note 2)	$I_{\text{SDM}}$	$V_{\text{GS}} = -5 \text{ V}, T_J = 25^\circ\text{C}$	–	–	69	A
Forward Diode Voltage	$V_{\text{SD}}$	$V_{\text{GS}} = -5 \text{ V}, I_{\text{SD}} = 6 \text{ A}, T_J = 25^\circ\text{C}$	–	4	10	V
Reverse Recovery Time	$t_{\text{RR}}$	$V_{\text{GS}} = -5/20 \text{ V}, I_{\text{SD}} = 16 \text{ A}, dI_{\text{SD}}/dt = 1000 \text{ A}/\mu\text{s}$	–	15	–	ns
Reverse Recovery Charge	$Q_{\text{RR}}$		–	45	–	nC
Reverse Recovery Energy	$E_{\text{REC}}$		–	3.9	–	$\mu\text{J}$
Peak Reverse Recovery Current	$I_{\text{RRM}}$		–	6.2	–	A
Charge Time	$T_a$		–	7.4	–	ns
Discharge Time	$T_b$		–	7	–	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

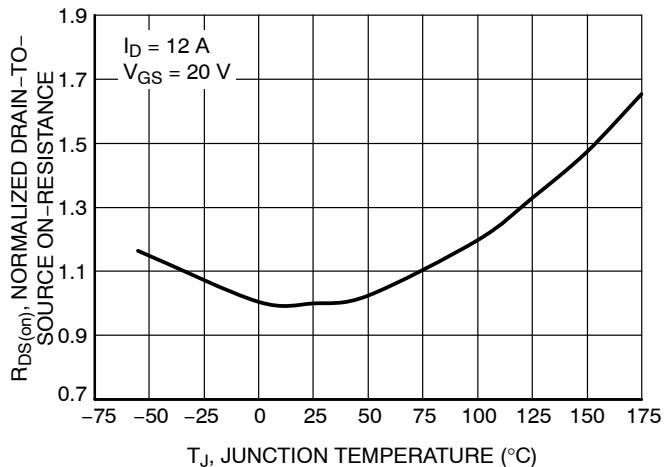
**TYPICAL CHARACTERISTICS**



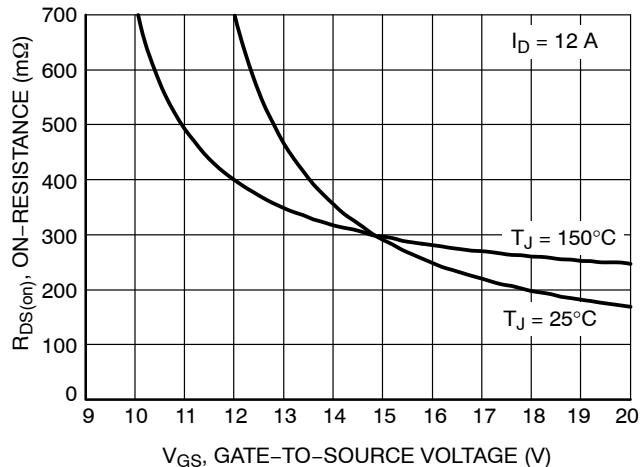
**Figure 1. On-Region Characteristics**



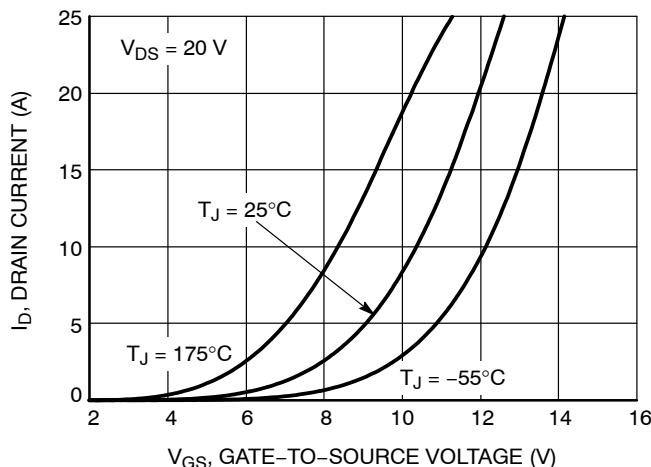
**Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage**



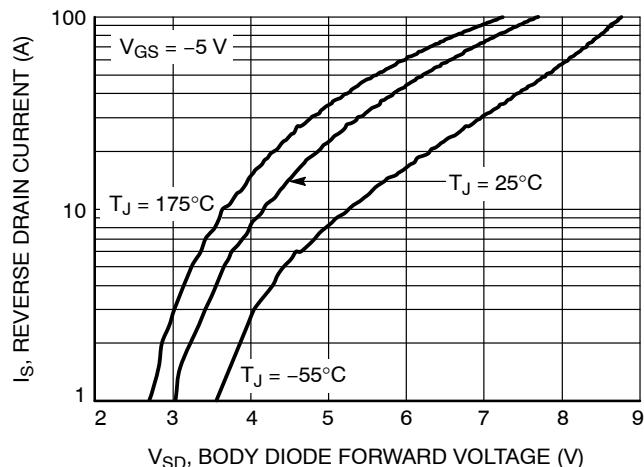
**Figure 3. On-Resistance Variation with Temperature**



**Figure 4. On-Resistance vs. Gate-to-Source Voltage**

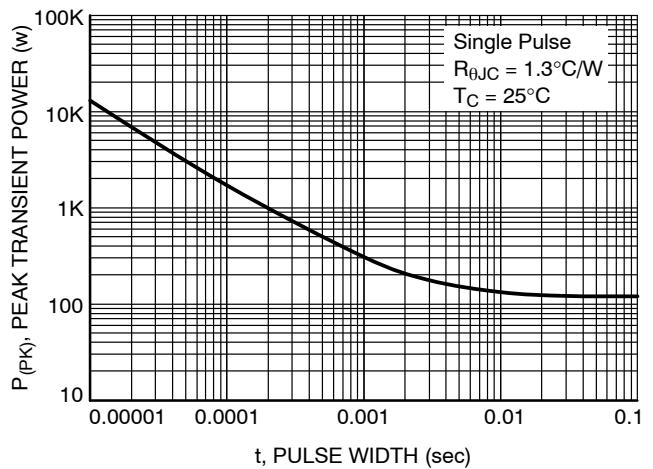
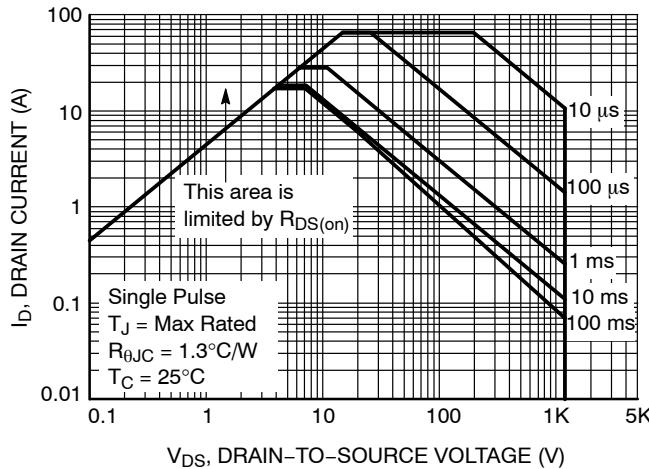
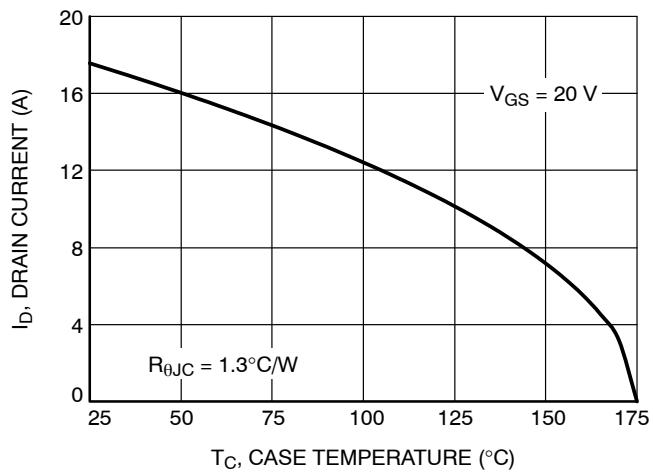
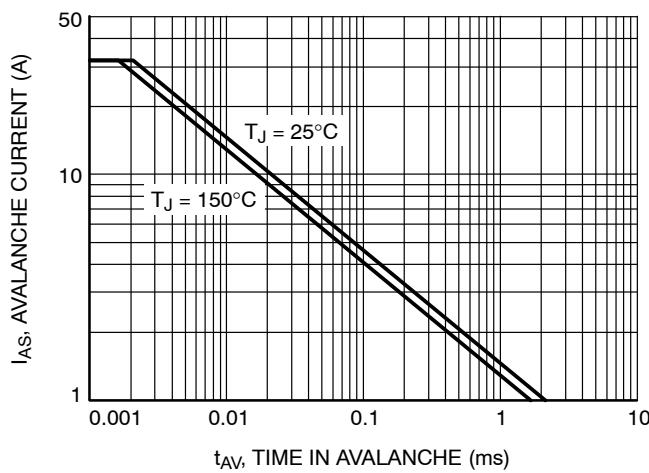
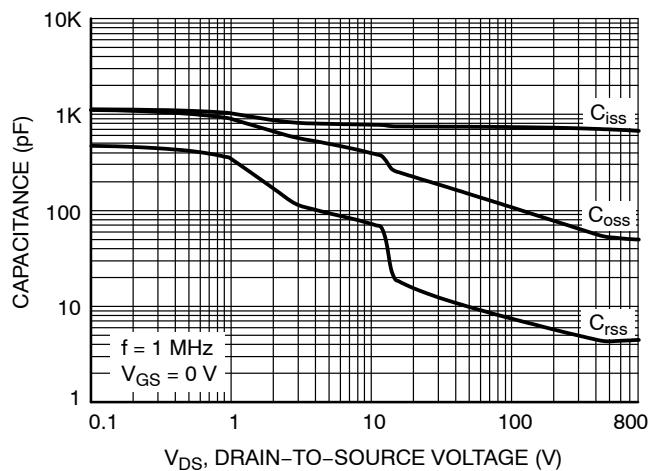
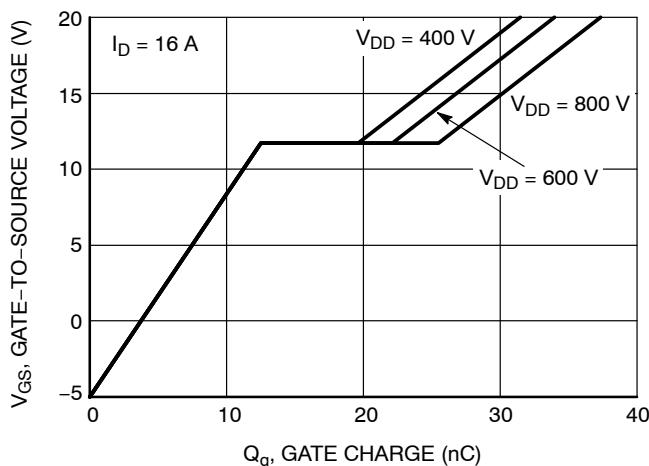


**Figure 5. Transfer Characteristics**



**Figure 6. Diode Forward Voltage vs. Current**

**TYPICAL CHARACTERISTICS**



# NTHL160N120SC1

## TYPICAL CHARACTERISTICS

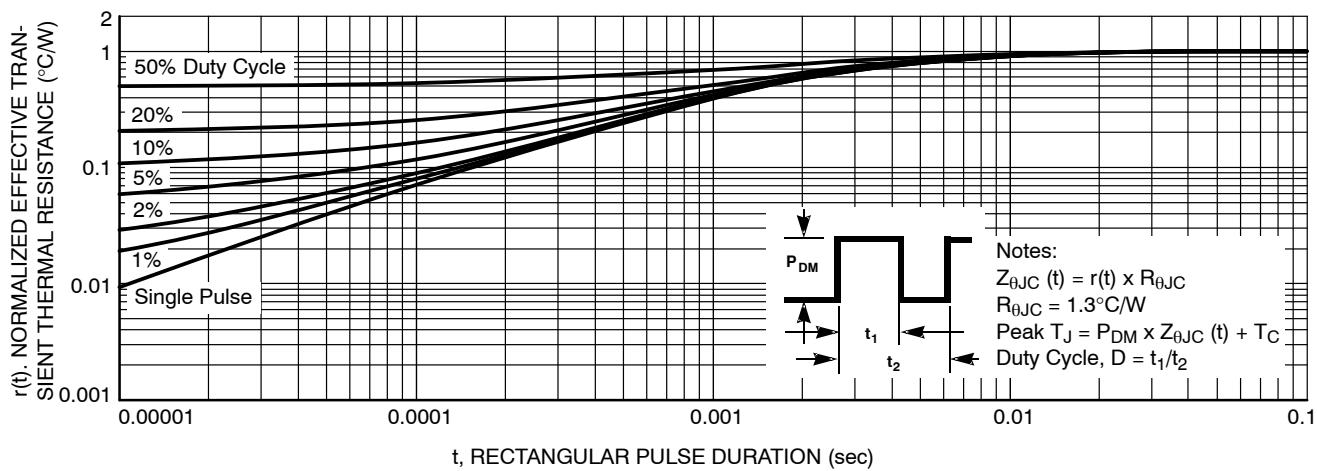


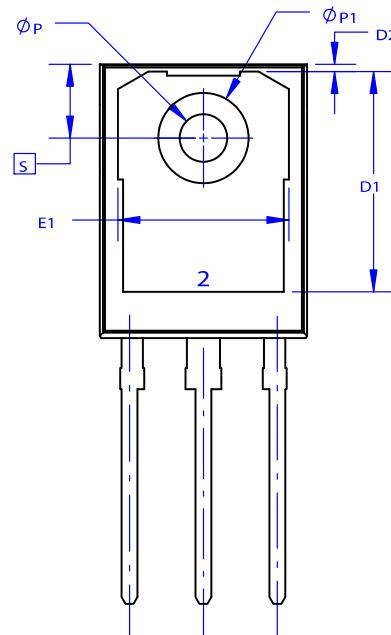
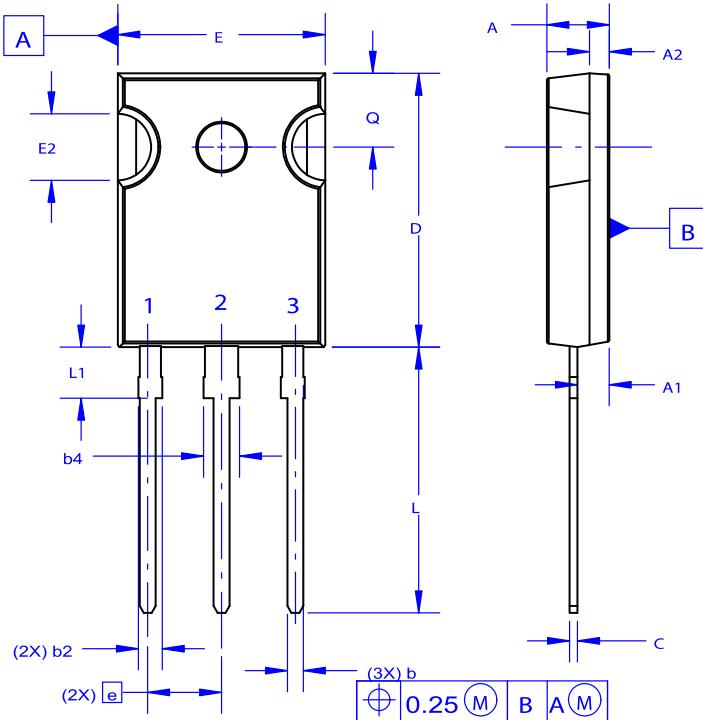
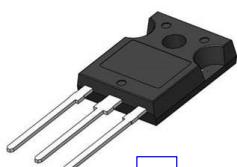
Figure 13. Junction-to-Ambient Thermal Response

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTHL160N120SC1	NTHL160N120SC1	TO-247 Long Lead	Tube	N/A	N/A	30 Units

TO-247-3LD  
CASE 340CX  
ISSUE A

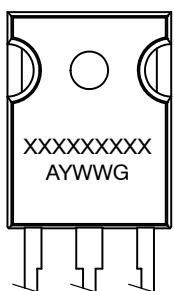
DATE 06 JUL 2020



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

**GENERIC  
MARKING DIAGRAM\***



XXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ΦP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ΦP1	6.60	6.80	7.00

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